

/ Descriptions

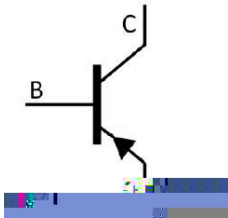
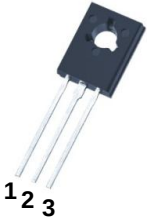
TO-126

PNP

Silicon PNP transistor in a TO-126 Plastic Package.

/ Features V_{CEO} High V_{CEO} Large DC current, high f_T , low $V_{CE(sat)}$.**/ Applications**

Low power audio amplifier, high speed switching applications.

/ Equivalent Circuit**/ Pinning**

PIN1 Emitter

PIN 2 Collector

PIN 3 Base

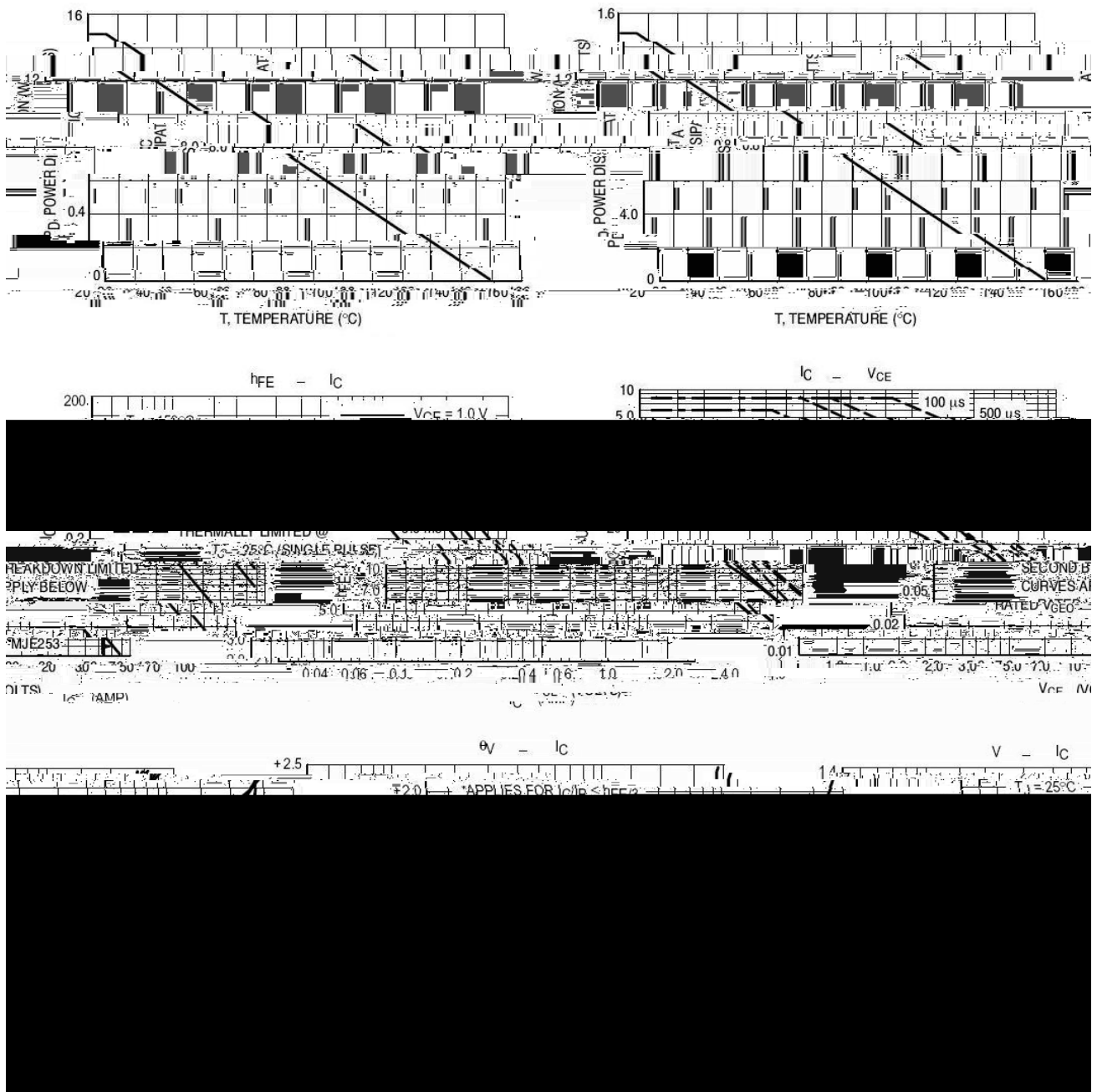
/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	$I_{C(1)}$	-4.0	A
	$I_{C(2)}$	-8.0	A
Peak Collector Current	I_B	-10	A
Collector Power Dissipation	P_D	1.5	W
Collector Power Dissipation	$P_D(T_c=25^\circ C)$	15	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min
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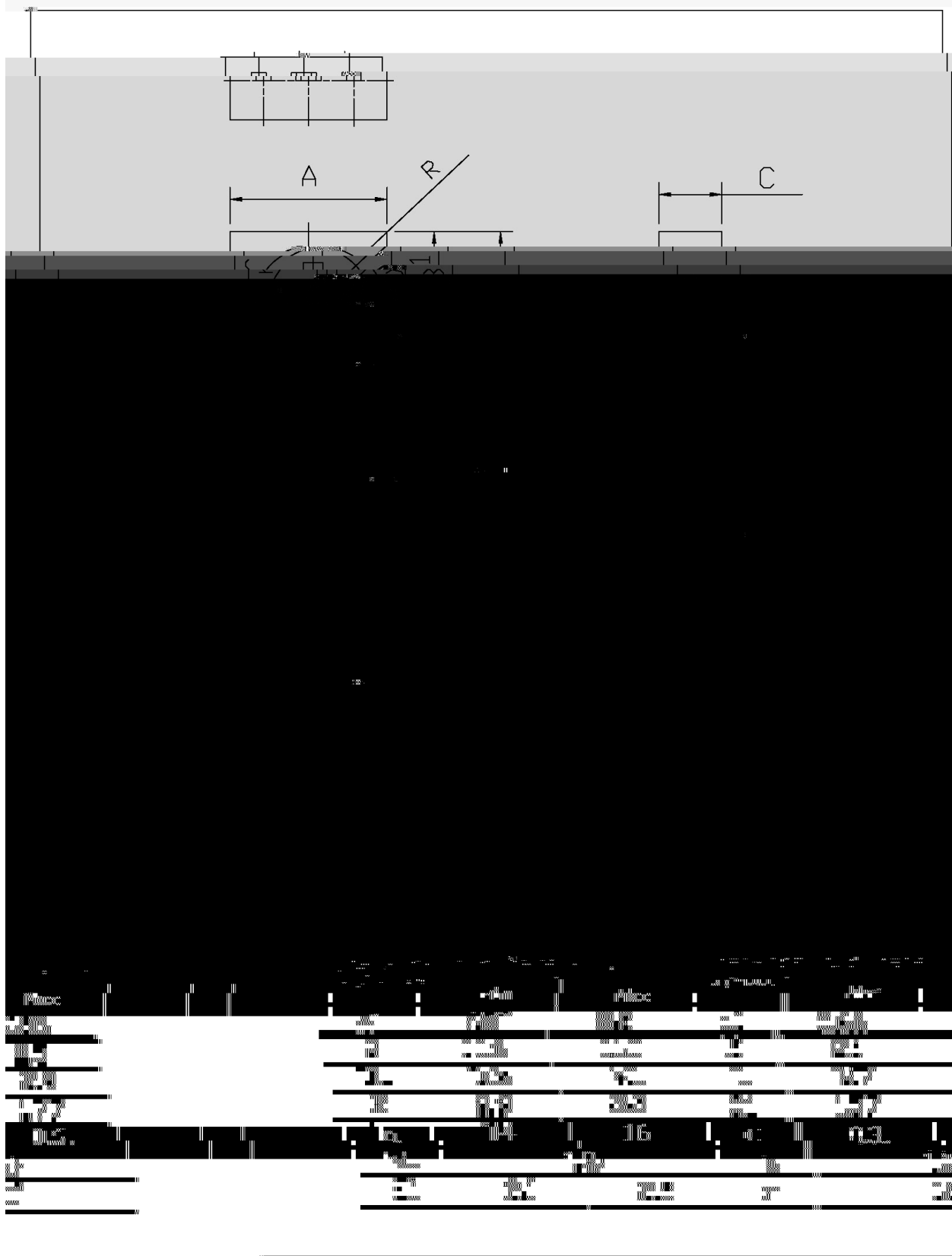
/ Electrical Characteristic Curve



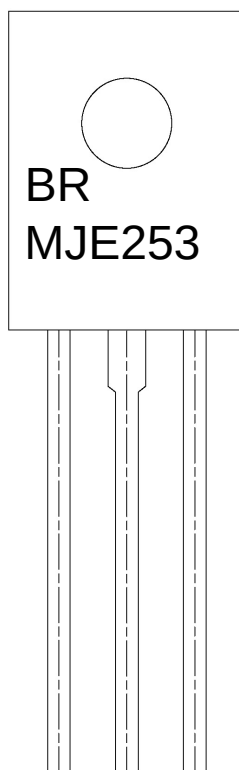
/ Package Dimensions

T□-126

单位: mm



/ Marking Instructions



BR

MJE253

Note:

BR: Company Code

MJE253: Product Type.

****: Lot No. Code, code change with Lot No.

